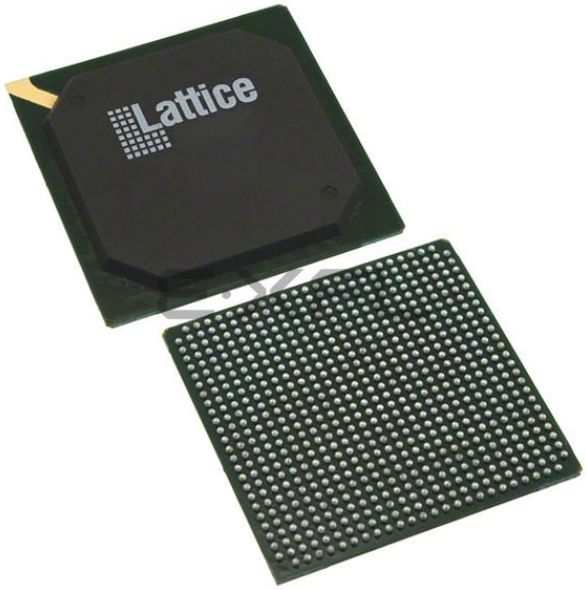
Lattice Semiconductor Corporation - LFE3-95EA-7LFN672C Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	11500
Number of Logic Elements/Cells	92000
Total RAM Bits	4526080
Number of I/O	380
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	672-BBGA
Supplier Device Package	672-FPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-95ea-7lfn672c

Architecture Overview

Each LatticeECP3 device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM™ Embedded Block RAM (EBR) and rows of sysDSP™ Digital Signal Processing slices, as shown in Figure 2-1. The LatticeECP3-150 has four rows of DSP slices; all other LatticeECP3 devices have two rows of DSP slices. In addition, the LatticeECP3 family contains SERDES Quads on the bottom of the device.

There are two kinds of logic blocks, the Programmable Functional Unit (PFU) and Programmable Functional Unit without RAM (PFF). The PFU contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFF block contains building blocks for logic, arithmetic and ROM functions. Both PFU and PFF blocks are optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array. Only one type of block is used per row.

The LatticeECP3 devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18Kbit fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, LatticeECP3 devices contain up to two rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The LatticeECP3 devices feature up to 16 embedded 3.2 Gbps SERDES (Serializer / Deserializer) channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of four SERDES channels, along with its Physical Coding Sub-layer (PCS) block, creates a quad. The functionality of the SERDES/PCS quads can be controlled by memory cells set during device configuration or by registers that are addressable during device operation. The registers in every quad can be programmed via the SERDES Client Interface (SCI). These quads (up to four) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysI/O buffers. The sysI/O buffers of the LatticeECP3 devices are arranged in seven banks, allowing the implementation of a wide variety of I/O standards. In addition, a separate I/O bank is provided for the programming interfaces. 50% of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit/receive pairs. The PIC logic also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3.

The LatticeECP3 registers in PFU and sysI/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The LatticeECP3 architecture provides two Delay Locked Loops (DLLs) and up to ten Phase Locked Loops (PLLs). The PLL and DLL blocks are located at the end of the EBR/DSP rows.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located toward the center of this EBR row. Every device in the LatticeECP3 family supports a sysCONFIG™ port located in the corner between banks one and two, which allows for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The LatticeECP3 devices use 1.2 V as their core voltage.

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/Subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/Down counter with asynchronous clear
- Up/Down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
  - A greater-than-or-equal-to B
  - A not-equal-to B
  - A less-than-or-equal-to B

Ripple Mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per slice basis to allow fast arithmetic functions to be constructed by concatenating Slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals. A 16x2-bit pseudo dual port RAM (PDPR) memory is created by using one Slice as the read-write port and the other companion slice as the read-only port.

LatticeECP3 devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in LatticeECP3 devices, please see TN1179, LatticeECP3 Memory Usage Guide.

Table 2-3. Number of Slices Required to Implement Distributed RAM

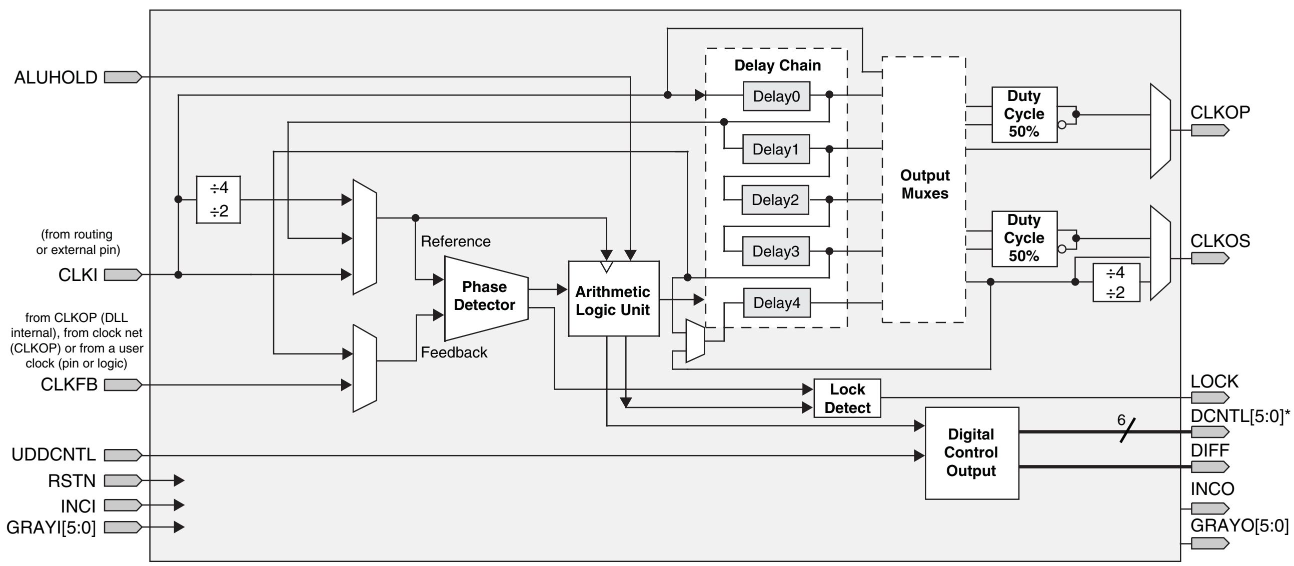
	SPR 16X4	PDPR 16X4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM chain in order to better match the reference and feedback signals. This digital code from the ALU is also transmitted via the Digital Control bus (DCNTL) bus to its associated Slave Delay lines (two per DLL). The ALUHOLD input allows the user to suspend the ALU output at its current value. The UDDCNTL signal allows the user to latch the current value on the DCNTL bus.

The DLL has two clock outputs, CLKOP and CLKOS. These outputs can individually select one of the outputs from the tapped delay line. The CLKOS has optional fine delay shift and divider blocks to allow this output to be further modified, if required. The fine delay shift block allows the CLKOS output to phase shifted a further 45, 22.5 or 11.25 degrees relative to its normal position. Both the CLKOS and CLKOP outputs are available with optional duty cycle correction. Divide by two and divide by four frequencies are available at CLKOS. The LOCK output signal is asserted when the DLL is locked. Figure 2-5 shows the DLL block diagram and Table 2-5 provides a description of the DLL inputs and outputs.

The user can configure the DLL for many common functions such as time reference delay mode and clock injection removal mode. Lattice provides primitives in its design tools for these functions.

Figure 2-5. Delay Locked Loop Diagram (DLL)

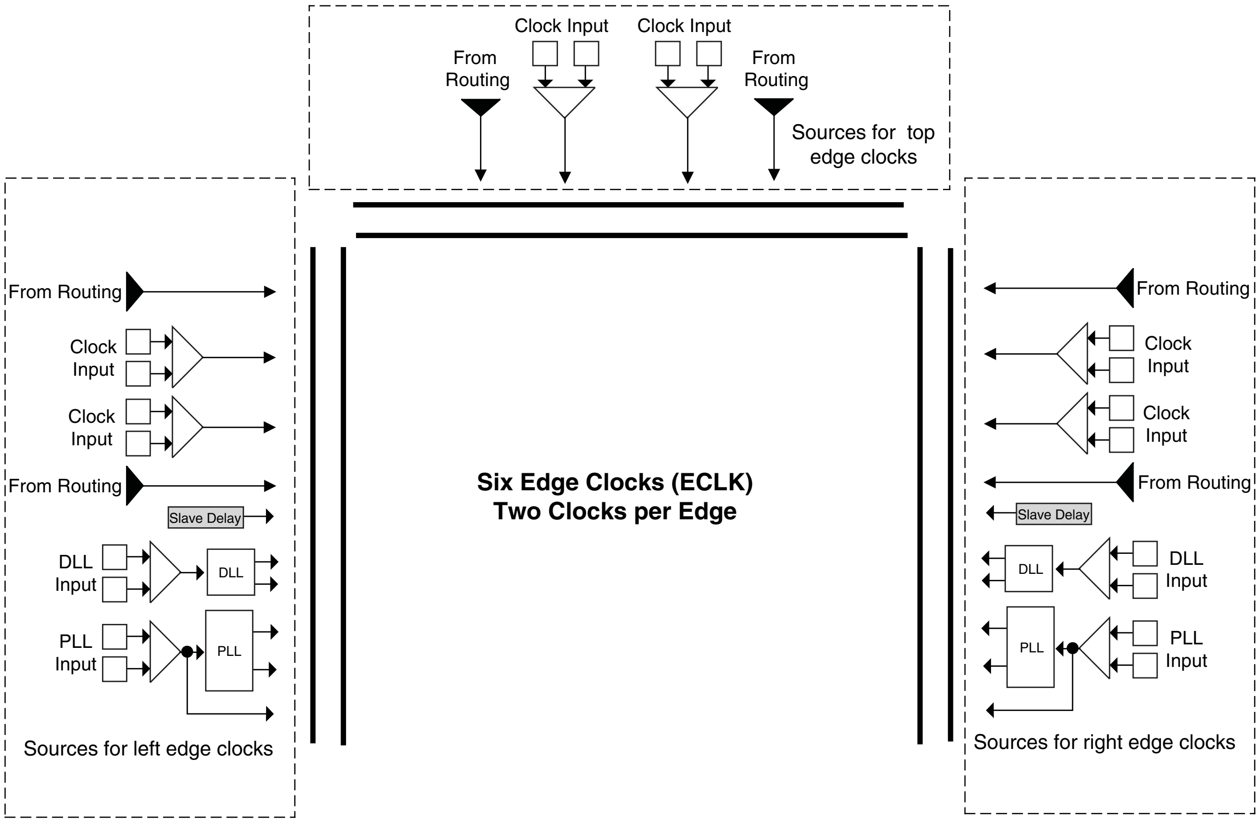


* This signal is not user accessible. This can only be used to feed the slave delay line.

Edge Clock Sources

Edge clock resources can be driven from a variety of sources at the same edge. Edge clock resources can be driven from adjacent edge clock PIOs, primary clock PIOs, PLLs, DLLs, Slave Delay and clock dividers as shown in Figure 2-19.

Figure 2-19. Edge Clock Sources



Notes:
1. Clock inputs can be configured in differential or single ended mode.
2. The two DLLs can also drive the two top edge clocks.
3. The top left and top right PLL can also drive the two top edge clocks.

Edge Clock Routing

LatticeECP3 devices have a number of high-speed edge clocks that are intended for use with the PIOs in the implementation of high-speed interfaces. There are six edge clocks per device: two edge clocks on each of the top, left, and right edges. Different PLL and DLL outputs are routed to the two muxes on the left and right sides of the device. In addition, the CLKINDEL signal (generated from the DLL Slave Delay Line block) is routed to all the edge clock muxes on the left and right sides of the device. Figure 2-20 shows the selection muxes for these clocks.

The edge clocks on the top, left, and right sides of the device can drive the secondary clocks or general routing resources of the device. The left and right side edge clocks also can drive the primary clock network through the clock dividers (CLKDIV).

sysMEM Memory

LatticeECP3 devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18-Kbit RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

sysMEM Memory Block

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as shown in Table 2-7. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with18-bit and 36-bit data widths. For more information, please see TN1179, LatticeECP3 Memory Usage Guide.

Table 2-7. sysMEM Block Configurations

Memory Mode	Configurations
Single Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36
True Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18
Pseudo Dual Port	16,384 x 1 8,192 x 2 4,096 x 4 2,048 x 9 1,024 x 18 512 x 36

Bus Size Matching

All of the multi-port memory modes support different widths on each of the ports. The RAM bits are mapped LSB word 0 to MSB word 0, LSB word 1 to MSB word 1, and so on. Although the word size and number of words for each port varies, this mapping scheme applies to each port.

RAM Initialization and ROM Operation

If desired, the contents of the RAM can be pre-loaded during device configuration. By preloading the RAM block during the chip configuration cycle and disabling the write controls, the sysMEM block can also be utilized as a ROM.

Memory Cascading

Larger and deeper blocks of RAM can be created using EBR sysMEM Blocks. Typically, the Lattice design tools cascade memory transparently, based on specific design inputs.

Control Logic Block

The control logic block allows the selection and modification of control signals for use in the PIO block.

DDR Memory Support

Certain PICs have additional circuitry to allow the implementation of high-speed source synchronous and DDR, DDR2 and DDR3 memory interfaces. The support varies by the edge of the device as detailed below.

Left and Right Edges

The left and right sides of the PIC have fully functional elements supporting DDR, DDR2, and DDR3 memory interfaces. One of every 12 PIOs supports the dedicated DQS pins with the DQS control logic block. Figure 2-35 shows the DQS bus spanning 11 I/O pins. Two of every 12 PIOs support the dedicated DQS and DQS# pins with the DQS control logic block.

Bottom Edge

PICs on the bottom edge of the device do not support DDR memory and Generic DDR interfaces.

Top Edge

PICs on the top side are similar to the PIO elements on the left and right sides but do not support gearing on the output registers. Hence, the modes to support output/tristate DDR3 memory are removed on the top side.

The exact DQS pins are shown in a dual function in the Logic Signal Connections table in this data sheet. Additional detail is provided in the Signal Descriptions table. The DQS signal from the bus is used to strobe the DDR data from the memory into input register blocks. Interfaces on the left, right and top edges are designed for DDR memories that support 10 bits of data.

Figure 2-35. DQS Grouping on the Left, Right and Top Edges

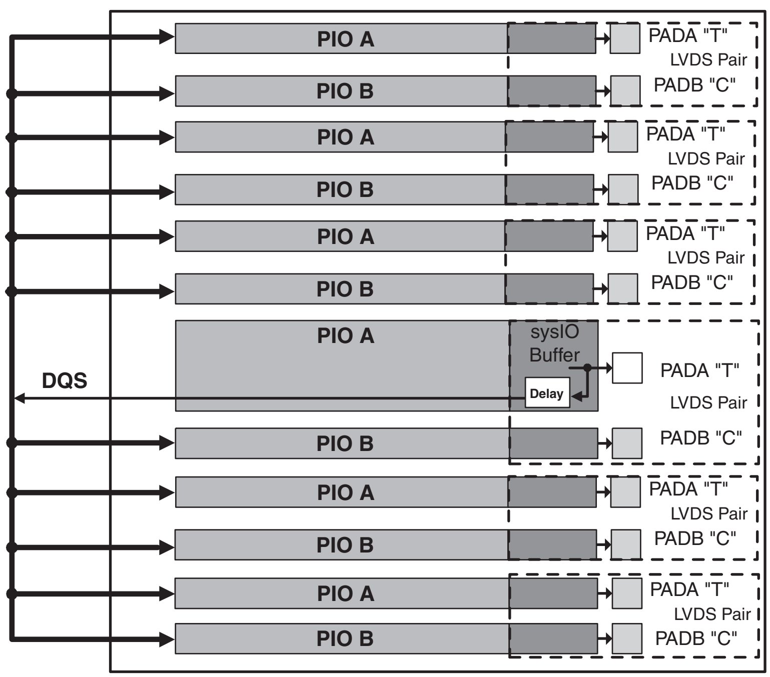
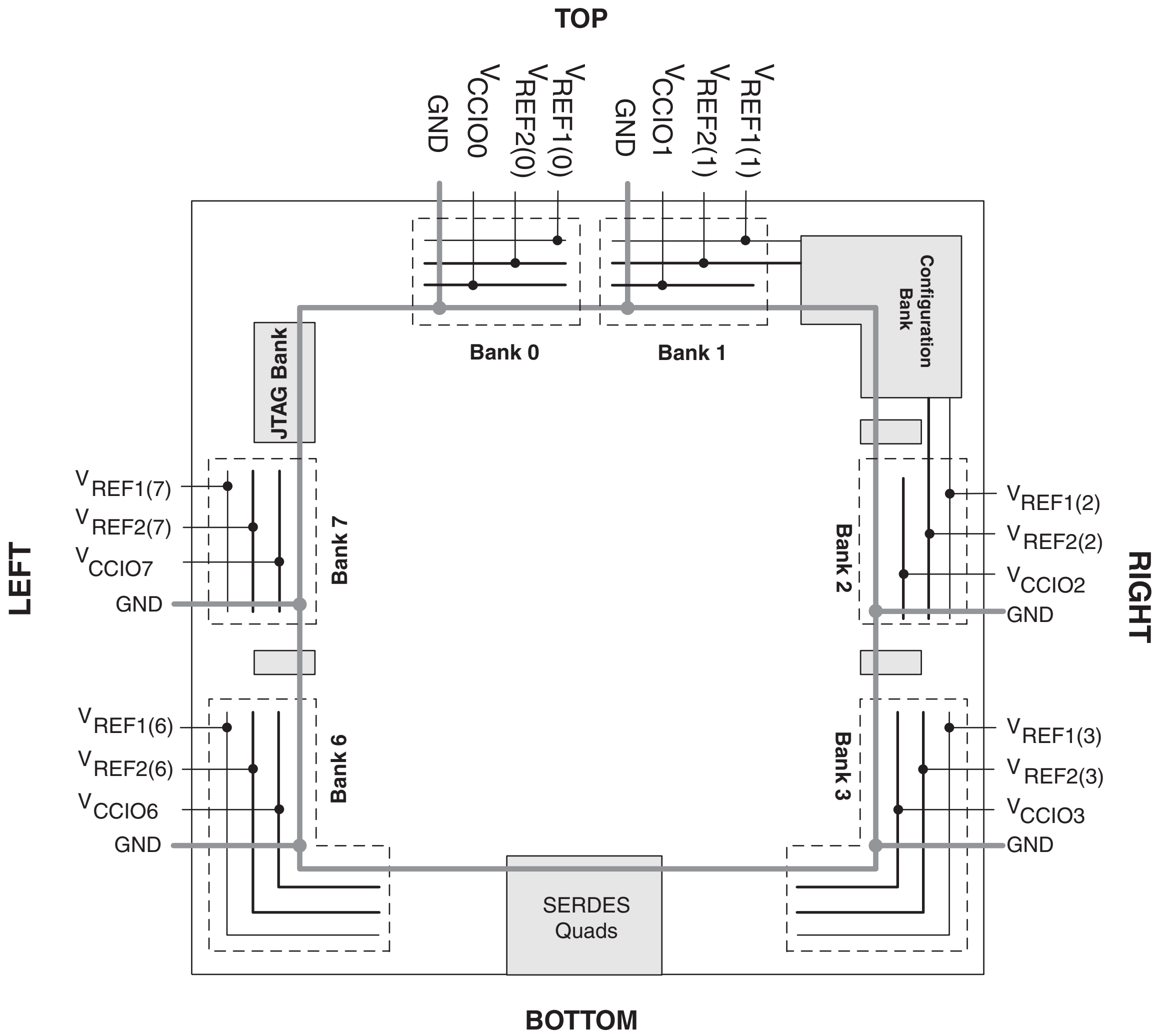


Figure 2-38. LatticeECP3 Banks



LatticeECP3 devices contain two types of sysI/O buffer pairs.

1. **Top (Bank 0 and Bank 1) and Bottom sysIO Buffer Pairs (Single-Ended Outputs Only)**
   The sysI/O buffer pairs in the top banks of the device consist of two single-ended output drivers and two sets of single-ended input buffers (both ratioed and referenced). One of the referenced input buffers can also be configured as a differential input. Only the top edge buffers have a programmable PCI clamp.

   The two pads in the pair are described as “true” and “comp”, where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

   The top and bottom sides are ideal for general purpose I/O, PCI, and inputs for LVDS (LVDS outputs are only allowed on the left and right sides). The top side can be used for the DDR3 ADDR/CMD signals.

   The I/O pins located on the top and bottom sides of the device (labeled PTxxA/B or PBxxA/B) are fully hot socketable. Note that the pads in Banks 3, 6 and 8 are wrapped around the corner of the device. In these banks, only the pads located on the top or bottom of the device are hot socketable. The top and bottom side pads can be identified by the Lattice Diamond tool.

There are some restrictions to be aware of when using spread spectrum. When a quad shares a PCI Express x1 channel with a non-PCI Express channel, ensure that the reference clock for the quad is compatible with all protocols within the quad. For example, a PCI Express spread spectrum reference clock is not compatible with most Gigabit Ethernet applications because of tight CTC ppm requirements.

While the LatticeECP3 architecture will allow the mixing of a PCI Express channel and a Gigabit Ethernet, Serial RapidIO or SGMII channel within the same quad, using a PCI Express spread spectrum clocking as the transmit reference clock will cause a violation of the Gigabit Ethernet, Serial RapidIO and SGMII transmit jitter specifications.

For further information on SERDES, please see TN1176, LatticeECP3 SERDES/PCS Usage Guide.

IEEE 1149.1-Compliant Boundary Scan Testability

All LatticeECP3 devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant Test Access Port (TAP). This allows functional testing of the circuit board on which the device is mounted through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port has its own supply voltage V_{CCJ} and can operate with LVCMOS3.3, 2.5, 1.8, 1.5 and 1.2 standards.

For more information, please see TN1169, LatticeECP3 sysCONFIG Usage Guide.

Device Configuration

All LatticeECP3 devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration, and the sysCONFIG port, support dual-byte, byte and serial configuration. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. The sysCONFIG port includes seven I/Os used as dedicated pins with the remaining pins used as dual-use pins. See TN1169, LatticeECP3 sysCONFIG Usage Guide for more information about using the dual-use pins as general purpose I/Os.

There are various ways to configure a LatticeECP3 device:

1. JTAG
2. Standard Serial Peripheral Interface (SPI and SPIm modes) - interface to boot PROM memory
3. System microprocessor to drive a x8 CPU port (PCM mode)
4. System microprocessor to drive a serial slave SPI port (SSPI mode)
5. Generic byte wide flash with a MachXO™ device, providing control and addressing

On power-up, the FPGA SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port.

LatticeECP3 devices also support the Slave SPI Interface. In this mode, the FPGA behaves like a SPI Flash device (slave mode) with the SPI port of the FPGA to perform read-write operations.

BLVDS25

The LatticeECP3 devices support the BLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel external resistor across the driver outputs. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS25 Multi-point Output Example

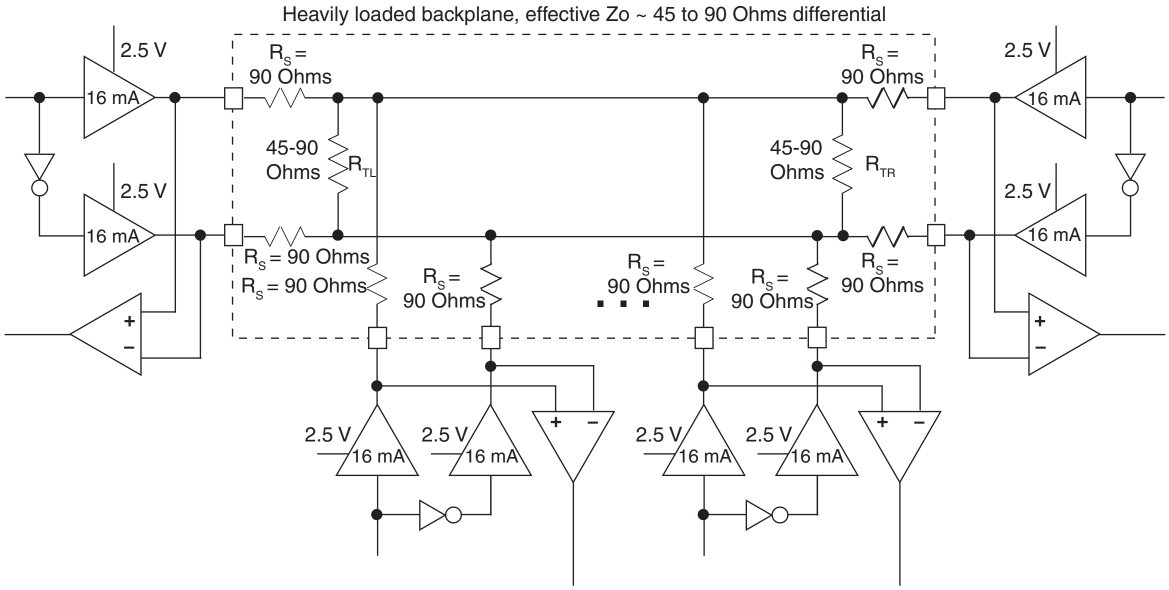


Table 3-2. BLVDS25 DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical		Units
		Zo = 45Ω	Zo = 90Ω	
V_{CCIO}	Output Driver Supply (+/– 5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (+/– 1%)	90.00	90.00	Ω
R_{TL}	Driver Parallel Resistor (+/– 1%)	45.00	90.00	Ω
R_{TR}	Receiver Termination (+/– 1%)	45.00	90.00	Ω
V_{OH}	Output High Voltage	1.38	1.48	V
V_{OL}	Output Low Voltage	1.12	1.02	V
V_{OD}	Output Differential Voltage	0.25	0.46	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	11.24	10.20	mA

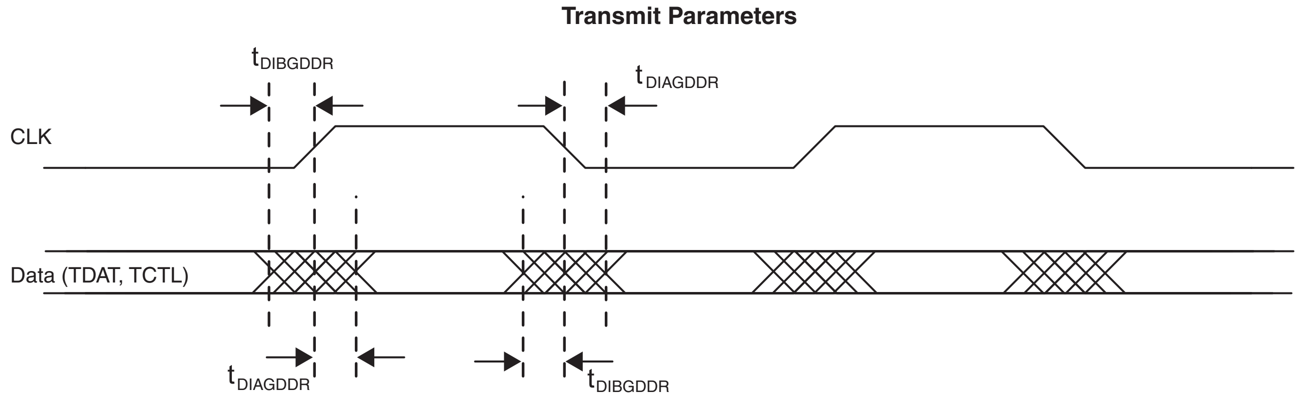
1. For input buffer, see LVDS table.

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-150EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.8	—	4.2	—	4.6	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
t_H	Clock to Data Hold - PIO Input Register	ECP3-70EA/95EA	1.4	—	1.6	—	1.8	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-70EA/95EA	1.3	—	1.5	—	1.7	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-70EA/95EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-70EA/95EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-35EA	—	3.7	—	4.1	—	4.5	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
t_H	Clock to Data Hold - PIO Input Register	ECP3-35EA	1.2	—	1.4	—	1.6	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-35EA	1.3	—	1.4	—	1.5	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-35EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-35EA	—	500	—	420	—	375	MHz
t_{CO}	Clock to Output - PIO Output Register	ECP3-17EA	—	3.5	—	3.9	—	4.3	ns
t_{SU}	Clock to Data Setup - PIO Input Register	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
t_H	Clock to Data Hold - PIO Input Register	ECP3-17EA	1.3	—	1.5	—	1.6	—	ns
t_{SU_DEL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-17EA	1.3	—	1.4	—	1.5	—	ns
t_{H_DEL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-17EA	0.0	—	0.0	—	0.0	—	ns
f_{MAX_IO}	Clock Frequency of I/O and PFU Register	ECP3-17EA	—	500	—	420	—	375	MHz
General I/O Pin Parameters Using Dedicated Clock Input Primary Clock with PLL with Clock Injection Removal Setting[2]									
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-150EA	—	3.3	—	3.6	—	39	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-150EA	0.7	—	0.8	—	0.9	—	ns
t_{HPLL}	Clock to Data Hold - PIO Input Register	ECP3-150EA	0.8	—	0.9	—	1.0	—	ns
t_{SU_DELPLL}	Clock to Data Setup - PIO Input Register with Data Input Delay	ECP3-150EA	1.6	—	1.8	—	2.0	—	ns
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Input Data Delay	ECP3-150EA	—	0.0	—	0.0	—	0.0	ns
t_{COPLL}	Clock to Output - PIO Output Register	ECP3-70EA/95EA	—	3.3	—	3.5	—	3.8	ns
t_{SUPLL}	Clock to Data Setup - PIO Input Register	ECP3-70EA/95EA	0.7	—	0.8	—	0.9	—	ns

Figure 3-6. Generic DDRX1/DDRX2 (With Clock and Data Edges Aligned)



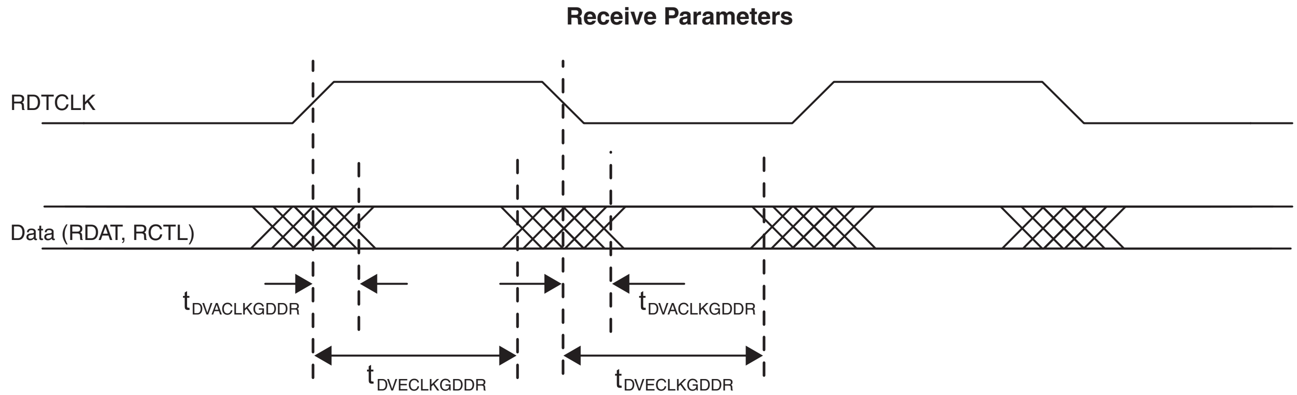
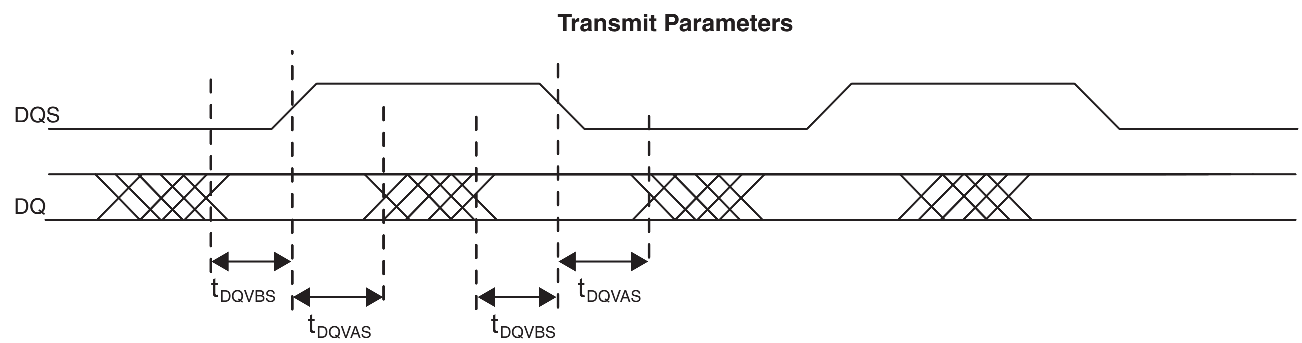
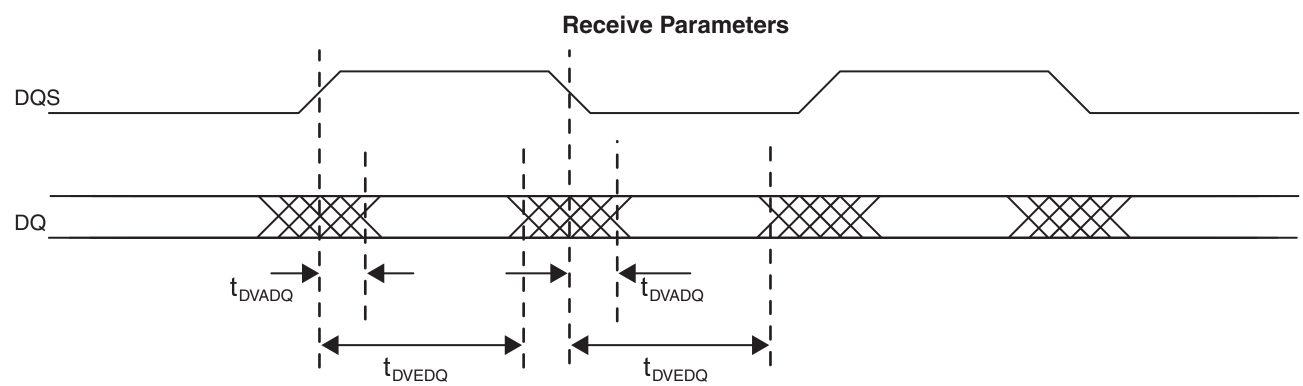


Figure 3-7. DDR/DDR2/DDR3 Parameters





LatticeECP3 Family Timing Adders[1, 2, 3, 4, 5, 7]

Over Recommended Commercial Operating Conditions

Buffer Type	Description	–8	–7	–6	Units
Input Adjusters					
LVDS25E	LVDS, Emulated, VCCIO = 2.5 V	0.03	–0.01	–0.03	ns
LVDS25	LVDS, VCCIO = 2.5 V	0.03	0.00	–0.04	ns
BLVDS25	BLVDS, Emulated, VCCIO = 2.5 V	0.03	0.00	–0.04	ns
MLVDS25	MLVDS, Emulated, VCCIO = 2.5 V	0.03	0.00	–0.04	ns
RSDS25	RSDS, VCCIO = 2.5 V	0.03	–0.01	–0.03	ns
PPLVDS	Point-to-Point LVDS	0.03	–0.01	–0.03	ns
TRLVDS	Transition-Reduced LVDS	0.03	0.00	–0.04	ns
Mini MLVDS	Mini LVDS	0.03	–0.01	–0.03	ns
LVPECL33	LVPECL, Emulated, VCCIO = 3.3 V	0.17	0.23	0.28	ns
HSTL18_I	HSTL_18 class I, VCCIO = 1.8 V	0.20	0.17	0.13	ns
HSTL18_II	HSTL_18 class II, VCCIO = 1.8 V	0.20	0.17	0.13	ns
HSTL18D_I	Differential HSTL 18 class I	0.20	0.17	0.13	ns
HSTL18D_II	Differential HSTL 18 class II	0.20	0.17	0.13	ns
HSTL15_I	HSTL_15 class I, VCCIO = 1.5 V	0.10	0.12	0.13	ns
HSTL15D_I	Differential HSTL 15 class I	0.10	0.12	0.13	ns
SSTL33_I	SSTL_3 class I, VCCIO = 3.3 V	0.17	0.23	0.28	ns
SSTL33_II	SSTL_3 class II, VCCIO = 3.3 V	0.17	0.23	0.28	ns
SSTL33D_I	Differential SSTL_3 class I	0.17	0.23	0.28	ns
SSTL33D_II	Differential SSTL_3 class II	0.17	0.23	0.28	ns
SSTL25_I	SSTL_2 class I, VCCIO = 2.5 V	0.12	0.14	0.16	ns
SSTL25_II	SSTL_2 class II, VCCIO = 2.5 V	0.12	0.14	0.16	ns
SSTL25D_I	Differential SSTL_2 class I	0.12	0.14	0.16	ns
SSTL25D_II	Differential SSTL_2 class II	0.12	0.14	0.16	ns
SSTL18_I	SSTL_18 class I, VCCIO = 1.8 V	0.08	0.06	0.04	ns
SSTL18_II	SSTL_18 class II, VCCIO = 1.8 V	0.08	0.06	0.04	ns
SSTL18D_I	Differential SSTL_18 class I	0.08	0.06	0.04	ns
SSTL18D_II	Differential SSTL_18 class II	0.08	0.06	0.04	ns
SSTL15	SSTL_15, VCCIO = 1.5 V	0.087	0.059	0.032	ns
SSTL15D	Differential SSTL_15	0.087	0.059	0.032	ns
LVTTL33	LVTTL, VCCIO = 3.3 V	0.07	0.07	0.07	ns
LVCMOS33	LVCMOS, VCCIO = 3.3 V	0.07	0.07	0.07	ns
LVCMOS25	LVCMOS, VCCIO = 2.5 V	0.00	0.00	0.00	ns
LVCMOS18	LVCMOS, VCCIO = 1.8 V	–0.13	–0.13	–0.13	ns
LVCMOS15	LVCMOS, VCCIO = 1.5 V	–0.07	–0.07	–0.07	ns
LVCMOS12	LVCMOS, VCCIO = 1.2 V	–0.20	–0.19	–0.19	ns
PCI33	PCI, VCCIO = 3.3 V	0.07	0.07	0.07	ns
Output Adjusters					
LVDS25E	LVDS, Emulated, VCCIO = 2.5 V	1.02	1.14	1.26	ns
LVDS25	LVDS, VCCIO = 2.5 V	–0.11	–0.07	–0.03	ns
BLVDS25	BLVDS, Emulated, VCCIO = 2.5 V	1.01	1.13	1.25	ns
MLVDS25	MLVDS, Emulated, VCCIO = 2.5 V	1.01	1.13	1.25	ns

LatticeECP3 Family Timing Adders[1, 2, 3, 4, 5, 7] (Continued)

Over Recommended Commercial Operating Conditions

Buffer Type	Description	–8	–7	–6	Units
LVCMOS15_4mA	LVCMOS 1.5 4 mA drive, fast slew rate	0.21	0.25	0.29	ns
LVCMOS15_8mA	LVCMOS 1.5 8 mA drive, fast slew rate	0.05	0.07	0.09	ns
LVCMOS12_2mA	LVCMOS 1.2 2 mA drive, fast slew rate	0.43	0.51	0.59	ns
LVCMOS12_6mA	LVCMOS 1.2 6 mA drive, fast slew rate	0.23	0.28	0.33	ns
LVCMOS33_4mA	LVCMOS 3.3 4 mA drive, slow slew rate	1.44	1.58	1.72	ns
LVCMOS33_8mA	LVCMOS 3.3 8 mA drive, slow slew rate	0.98	1.10	1.22	ns
LVCMOS33_12mA	LVCMOS 3.3 12 mA drive, slow slew rate	0.67	0.77	0.86	ns
LVCMOS33_16mA	LVCMOS 3.3 16 mA drive, slow slew rate	0.97	1.09	1.21	ns
LVCMOS33_20mA	LVCMOS 3.3 20 mA drive, slow slew rate	0.67	0.76	0.85	ns
LVCMOS25_4mA	LVCMOS 2.5 4 mA drive, slow slew rate	1.48	1.63	1.78	ns
LVCMOS25_8mA	LVCMOS 2.5 8 mA drive, slow slew rate	1.02	1.14	1.27	ns
LVCMOS25_12mA	LVCMOS 2.5 12 mA drive, slow slew rate	0.74	0.84	0.94	ns
LVCMOS25_16mA	LVCMOS 2.5 16 mA drive, slow slew rate	1.02	1.14	1.26	ns
LVCMOS25_20mA	LVCMOS 2.5 20 mA drive, slow slew rate	0.74	0.83	0.93	ns
LVCMOS18_4mA	LVCMOS 1.8 4 mA drive, slow slew rate	1.60	1.77	1.93	ns
LVCMOS18_8mA	LVCMOS 1.8 8 mA drive, slow slew rate	1.11	1.25	1.38	ns
LVCMOS18_12mA	LVCMOS 1.8 12 mA drive, slow slew rate	0.87	0.98	1.09	ns
LVCMOS18_16mA	LVCMOS 1.8 16 mA drive, slow slew rate	0.86	0.97	1.07	ns
LVCMOS15_4mA	LVCMOS 1.5 4 mA drive, slow slew rate	1.71	1.89	2.08	ns
LVCMOS15_8mA	LVCMOS 1.5 8 mA drive, slow slew rate	1.20	1.34	1.48	ns
LVCMOS12_2mA	LVCMOS 1.2 2 mA drive, slow slew rate	1.37	1.56	1.74	ns
LVCMOS12_6mA	LVCMOS 1.2 6 mA drive, slow slew rate	1.11	1.27	1.43	ns
PCI33	PCI, VCCIO = 3.3 V	–0.12	–0.13	–0.14	ns

1. Timing adders are characterized but not tested on every device.
2. LVCMOS timing measured with the load specified in Switching Test Condition table.
3. All other standards tested according to the appropriate specifications.
4. Not all I/O standards and drive strengths are supported for all banks. See the Architecture section of this data sheet for details.
5. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.
6. This data does not apply to the LatticeECP3-17EA device.
7. For details on –9 speed grade devices, please contact your Lattice Sales Representative.

Figure 3-14. Jitter Transfer – 3.125 Gbps

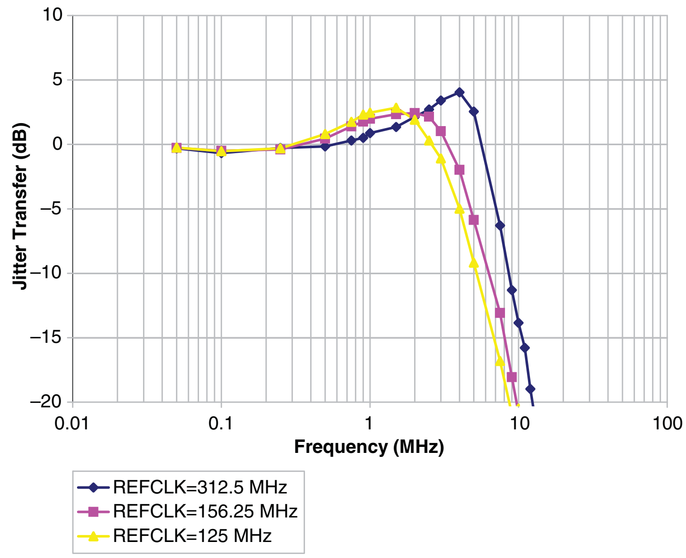
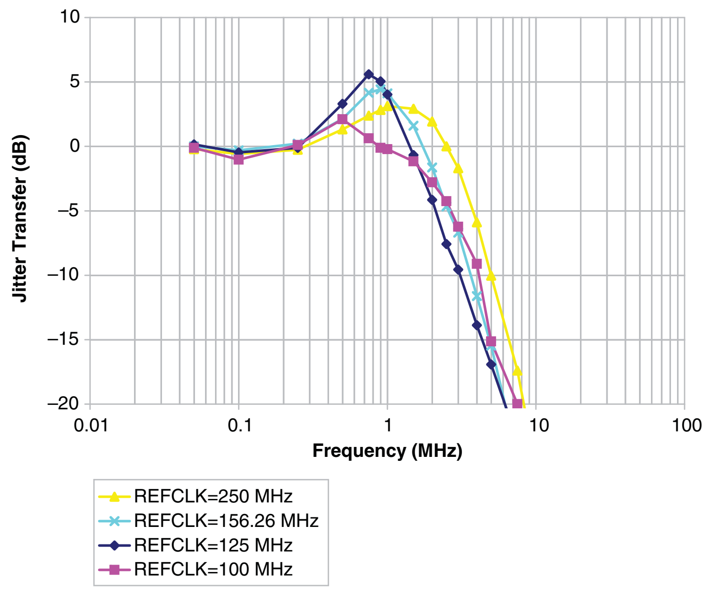


Figure 3-15. Jitter Transfer – 2.5 Gbps



LatticeECP3 sysCONFIG Port Timing Specifications

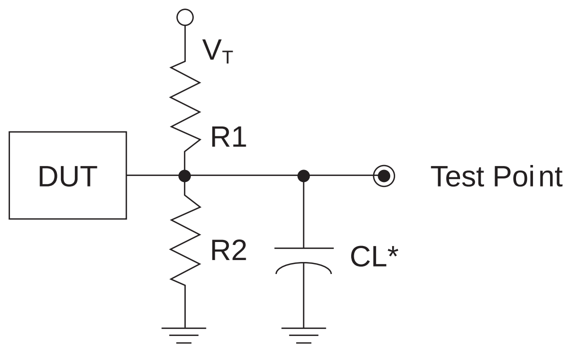
Over Recommended Operating Conditions

Parameter	Description		Min.	Max.	Units
POR, Configuration Initialization, and Wakeup					
t_{ICFG}	Time from the Application of V_{CC}, V_{CCAUX} or V_{CCIO8}* (Whichever is the Last to Cross the POR Trip Point) to the Rising Edge of INITN	Master mode	—	23	ms
		Slave mode	—	6	ms
t_{VMC}	Time from t_{ICFG} to the Valid Master MCLK		—	5	µs
t_{PRGM}	PROGRAMN Low Time to Start Configuration		25	—	ns
t_{PRGMRJ}	PROGRAMN Pin Pulse Rejection		—	10	ns
$t_{DPPINIT}$	Delay Time from PROGRAMN Low to INITN Low		—	37	ns
$t_{DPPDONE}$	Delay Time from PROGRAMN Low to DONE Low		—	37	ns
t_{DINIT}[1]	PROGRAMN High to INITN High Delay		—	1	ms
t_{MWC}	Additional Wake Master Clock Signals After DONE Pin is High		100	500	cycles
t_{CZ}	MCLK From Active To Low To High-Z		—	300	ns
t_{IODISS}	User I/O Disable from PROGRAMN Low		—	100	ns
t_{IOENSS}	User I/O Enabled Time from CCLK Edge During Wake-up Sequence		—	100	ns
All Configuration Modes					
t_{SUCDI}	Data Setup Time to CCLK/MCLK		5	—	ns
t_{HCDI}	Data Hold Time to CCLK/MCLK		1	—	ns
t_{CODO}	CCLK/MCLK to DOUT in Flowthrough Mode		-0.2	12	ns
Slave Serial					
t_{SSCH}	CCLK Minimum High Pulse		5	—	ns
t_{SSCL}	CCLK Minimum Low Pulse		5	—	ns
f_{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave Parallel					
t_{SUCS}	CSN[1:0] Setup Time to CCLK/MCLK		7	—	ns
t_{HCS}	CSN[1:0] Hold Time to CCLK/MCLK		1	—	ns
t_{SUWD}	WRITEN Setup Time to CCLK/MCLK		7	—	ns
t_{HWD}	WRITEN Hold Time to CCLK/MCLK		1	—	ns
t_{DCB}	CCLK/MCLK to BUSY Delay Time		—	12	ns
t_{CORD}	CCLK to Out for Read Data		—	12	ns
t_{BSCH}	CCLK Minimum High Pulse		6	—	ns
t_{BSCL}	CCLK Minimum Low Pulse		6	—	ns
t_{BSCYC}	Byte Slave Cycle Time		30	—	ns
f_{CCLK}	CCLK/MCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
Master and Slave SPI					
t_{CFGX}	INITN High to MCLK Low		—	80	ns
t_{CSSPI}	INITN High to CSSPIN Low		0.2	2	µs
t_{SOCDO}	MCLK Low to Output Valid		—	15	ns
t_{CSPID}	CSSPIN[0:1] Low to First MCLK Edge Setup Time		0.3		µs
f_{CCLK}	CCLK Frequency	Without encryption	—	33	MHz
		With encryption	—	20	MHz
t_{SSCH}	CCLK Minimum High Pulse		5	—	ns

Switching Test Conditions

Figure 3-33 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-23.

Figure 3-33. Output Test Load, LVTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

Table 3-23. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R_1	R_2	C_L	Timing Ref.	V_T
LVTTL and other LVCMOS settings (L -> H, H -> L)	∞	∞	0 pF	LVCMOS 3.3 = 1.5V	—
				LVCMOS 2.5 = $V_{CCIO}/2$	—
				LVCMOS 1.8 = $V_{CCIO}/2$	—
				LVCMOS 1.5 = $V_{CCIO}/2$	—
				LVCMOS 1.2 = $V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> H)	∞	1MΩ	0 pF	$V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> L)	1 MΩ	∞	0 pF	$V_{CCIO}/2$	V_{CCIO}
LVCMOS 2.5 I/O (H -> Z)	∞	100	0 pF	V_{OH} - 0.10	—
LVCMOS 2.5 I/O (L -> Z)	100	∞	0 pF	V_{OL} + 0.10	V_{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.

PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO Within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ
For Top Edge of the Device		
P[Edge] [n-3]	A	DQ
	B	DQ
P[Edge] [n-2]	A	DQ
	B	DQ
P[Edge] [n-1]	A	DQ
	B	DQ
P[Edge] [n]	A	[Edge]DQSn
	B	DQ
P[Edge] [n+1]	A	DQ
	B	DQ
P[Edge] [n+2]	A	DQ
	B	DQ

Note: “n” is a row PIC number.

Pin Information Summary (Cont.)

Pin Information Summary		ECP3-17EA			ECP3-35EA		
Pin Type		256 ftBGA	328 csBGA	484 fpBGA	256 ftBGA	484 fpBGA	672 fpBGA
Emulated Differential I/O per Bank	Bank 0	13	10	18	13	21	24
	Bank 1	7	5	12	7	18	18
	Bank 2	2	2	4	1	8	8
	Bank 3	4	2	13	5	20	19
	Bank 6	5	1	13	6	22	20
	Bank 7	6	9	10	6	11	13
	Bank 8	12	12	12	12	12	12
Highspeed Differential I/O per Bank	Bank 0	0	0	0	0	0	0
	Bank 1	0	0	0	0	0	0
	Bank 2	2	2	3	3	6	6
	Bank 3	5	4	9	4	9	12
	Bank 6	5	4	9	4	11	12
	Bank 7	5	6	8	5	9	10
	Bank 8	0	0	0	0	0	0
Total Single Ended/ Total Differential I/O per Bank	Bank 0	26/13	20/10	36/18	26/13	42/21	48/24
	Bank 1	14/7	10/5	24/12	14/7	36/18	36/18
	Bank 2	8/4	9/4	14/7	8/4	28/14	28/14
	Bank 3	18/9	12/6	44/22	18/9	58/29	63/31
	Bank 6	20/10	11/5	44/22	20/10	67/33	65/32
	Bank 7	23/11	30/15	36/18	23/11	40/20	46/23
	Bank 8	24/12	24/12	24/12	24/12	24/12	24/12
DDR Groups Bonded per Bank[2]	Bank 0	2	1	3	2	3	4
	Bank 1	1	0	2	1	3	3
	Bank 2	0	0	1	0	2	2
	Bank 3	1	0	3	1	3	4
	Bank 6	1	0	3	1	4	4
	Bank 7	1	2	2	1	3	3
	Configuration Bank 8	0	0	0	0	0	0
SERDES Quads		1	1	1	1	1	1

1. These pins must remain floating on the board.
2. Some DQS groups may not support DQS-12. Refer to the device pinout (.csv) file.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672C	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672C	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672C	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6LFN672C	1.2 V	–6	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7LFN672C	1.2 V	–7	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8LFN672C	1.2 V	–8	LOW	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156C	1.2 V	–6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156C	1.2 V	–7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156C	1.2 V	–8	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-6LFN1156C	1.2 V	–6	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7LFN1156C	1.2 V	–7	LOW	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8LFN1156C	1.2 V	–8	LOW	Lead-Free fpBGA	1156	COM	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672CTW[1]	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-7FN672CTW[1]	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-8FN672CTW[1]	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	149
LFE3-150EA-6FN1156CTW[1]	1.2 V	–6	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-7FN1156CTW[1]	1.2 V	–7	STD	Lead-Free fpBGA	1156	COM	149
LFE3-150EA-8FN1156CTW[1]	1.2 V	–8	STD	Lead-Free fpBGA	1156	COM	149

1. Note: Specifications for the LFE3-150EA-*sp*FN*pkg*CTW and LFE3-150EA-*sp*FN*pkg*ITW devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*sp*FN*pkg*C and LFE3-150EA-*sp*FN*pkg*I devices respectively, except as specified below.
   - The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.
   - The SERDES XRES pin on the TW device passes CDM testing at 250 V.

Date	Version	Section	Change Summary
March 2010	01.6	Architecture	Added Read-Before-Write information.
		DC and Switching Characteristics	Added footnote #6 to Maximum I/O Buffer Speed table.
			Corrected minimum operating conditions for input and output differential voltages in the Point-to-Point LVDS table.
		Pinout Information	Added pin information for the LatticeECP3-70EA and LatticeECP3-95EA devices.
		Ordering Information	Added ordering part numbers for the LatticeECP3-70EA and LatticeECP3-95EA devices.
			Removed dual mark information.
November 2009	01.5	Introduction	Updated Embedded SERDES features.
			Added SONET/SDH to Embedded SERDES protocols.
		Architecture	Updated Figure 2-4, General Purpose PLL Diagram.
			Updated SONET/SDH to SERDES and PCS protocols.
			Updated Table 2-13, SERDES Standard Support to include SONET/SDH and updated footnote 2.
		DC and Switching Characterisitcs	Added footnote to ESD Performance table.
			Updated SERDES Power Supply Requirements table and footnotes.
			Updated Maximum I/O Buffer Speed table.
			Updated Pin-to-Pin Peformance table.
			Updated sysCLOCK PLL Timing table.
			Updated DLL timing table.
			Updated High-Speed Data Transmitter tables.
			Updated High-Speed Data Receiver table.
			Updated footnote for Receiver Total Jitter Tolerance Specification table.
			Updated Periodic Receiver Jitter Tolerance Specification table.
			Updated SERDES External Reference Clock Specification table.
			Updated PCI Express Electrical and Timing AC and DC Characteristics.
			Deleted Reference Clock table for PCI Express Electrical and Timing AC and DC Characteristics.
			Updated SMPTE AC/DC Characteristics Transmit table.
			Updated Mini LVDS table.
			Updated RSDS table.
			Added Supply Current (Standby) table for EA devices.
			Updated Internal Switching Characteristics table.
			Updated Register-to-Register Performance table.
			Added HDMI Electrical and Timing Characteristics data.
			Updated Family Timing Adders table.
			Updated sysCONFIG Port Timing Specifications table.
			Updated Recommended Operating Conditions table.
			Updated Hot Socket Specifications table.
			Updated Single-Ended DC table.
			Updated TRLVDS table and figure.
			Updated Serial Data Input Specifications table.
			Updated HDMI Transmit and Receive table.
		Ordering Information	Added LFE3-150EA “TW” devices and footnotes to the Commercial and Industrial tables.